

DOCKET: 2755

PATENT

**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

In re Application: Seung Ho Park

Serial No.: 10/034,221

Filed: December 28, 2001

For: METHOD FOR FABRICATING A  
SEMICONDUCTOR EPITAXIAL WAFER  
HAVING DOPED CARBON AND A  
SEMICONDUCTOR EPITAXIAL WAFER



GRP ART UNIT

Ex.

**COPY OF PAPERS  
ORIGINALLY FILED**

---

THE COMMISSIONER FOR PATENTS  
Washington, D.C. 20231

**INFORMATION DISCLOSURE STATEMENT**

Applicants submit herewith several copies of U.S. Patents and Japanese patent applications of which the applicants are aware, and which may be material to the examination of this application and in respect of which there may be a duty to disclose under 37 CFR 1.56.

The filing of this information disclosure statement shall not be construed as a representation that a search has been made (37 CFR 1.97(g)), an admission that the information cited is, or is considered to be, material to patentability or that no other material information exists.

The filing of this information disclosure statement shall not be construed as an admission against interest in any manner. Notice of January 9, 1992, 1135 O.G. 13-25, at 25.

The references submitted herewith are listed on PTO-Form 1449 (modified) attached hereto. A copy of each reference listed patent is being furnished.

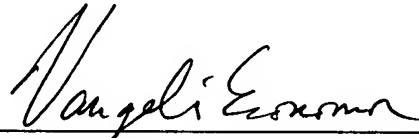
Additional comments, if any, on the relevance of each reference listed are provided as follows:

Full translations of the Japanese applications are not readily available, but a Japanese language Abstract is attached to each of the Japanese applications.

The Statement is made on the basis of the information:

<u>          </u>	supplied by the inventor(s);
<u>  X  </u>	supplied by an individual associated with the filing and prosecution
<u>          </u>	of this application (37 CFR 1.56(c)); or
<u>          </u>	in the attorney's file.

Respectfully submitted,



Vangelis Economou -Reg. No.-32,341  
Ladas & Parry  
224 South Michigan Avenue  
Chicago Illinois 60604  
Tel. No. (312) 427-1300

Feb. 25, 2002

Date

2800  
2812 0430  
DOCKET: 2755

# 2  
BT  
6.10-02  
PATENT

**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

In re Application: Seung Ho PYI

Serial No.: 10/034,221

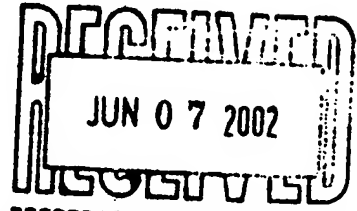
Filed: December 28, 2001

For: METHOD FOR FABRICATING A  
SEMICONDUCTOR EPITAXIAL WAFER  
HAVING DOPED CARBON AND A  
SEMICONDUCTOR EPITAXIAL WAFER



GRP ART UNIT

Ex.



COPY OF PAPERS  
ORIGINALLY FILED

**Certification under 37 C.F.R. §1.8(a)**

I hereby certify that this paper (along with any paper referred to as being attached or enclosed) is being deposited with The United States Postal Service with sufficient postage as first class mail in an envelope addressed to The Commissioner for Patents, Washington, D.C. 20231 on February 26, 2002.

*Vangelis Economou*  
Vangelis Economou - Reg. No. 32,341

Commissioner for Patents  
Washington, D.C. 20231

**TRANSMITTAL OF INFORMATION DISCLOSURE STATEMENT WITHIN THREE MONTHS  
OF FILING OR BEFORE MAILING OF FIRST OFFICE ACTION**

Sir:

The information disclosure statement submitted herewith is being filed within three months of the filing date of the application or date of entry into the national stage of an international application or before the mailing date of the first Office Action on the merits, whichever event occurs last. 37 CFR 1.97(b).

February 25, 2002

*Vangelis Economou*  
Vangelis Economou - Reg. No. 32,341  
Ladas & Parry  
224 South Michigan Avenue  
Chicago Illinois 60604  
Tel. No. (312) 427-1300

idsb40a